Darlington Power Transistor





Description

Complementary silicon power transistor.

The MJ15003 power transistor designed for high power audio, disk head positions and other linear applications.

Features

- High safe operating area (100% tested) 5A at 50V
- · For low distortion complementary designs
- High DC current gain hFE = 25 (minimum) at Ic = 5A DC
- · Pb-free package

Maximum Ratings (Note 1)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	Vceo	140	V DC
Collector-Base Voltage	Vсво	140	
Emitter-Base Voltage	VEBO	5	
Collector Current - Continuous	lc	20	A DC
Base Current - Continuous	Ів	5	
Emitter Current - Continuous	lε	25	
Total Device Dissipation at TC = 25°C Derate above 25°C	Po	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	-65 to +200	°C

Thermal Characteristics

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.7	°C / W
Maximum Lead Temperature for Soldering Purpose 1/6 inches from Case for ≤10 Seconds	TL	265	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

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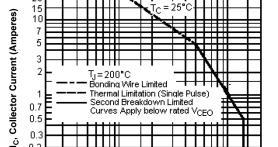


Electrical Characteristics (Tc = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
Off Characteristics				
Collector-Emitter Sustaining Voltage (Note 1) $(I_C = 200 \text{mA DC}, I_B = 0)$	V _{EO(sus)}	140	-	V DC
Collector Cut off Current $(V_{CE} = 140 \text{V DC}, V_{BE \text{ (off)}} = 1.5 \text{V DC})$ $(V_{CE} = 140 \text{V DC}, V_{BE \text{ (off)}} = 1.5 \text{V DC}, T_{C} = 150 ^{\circ}\text{C})$	I _{CEX}	1	100 2	μA DC mA DC
Collector Cut off Current (V _{CE} = 140V DC, I _B = 0)	I _{CEO}	1	250	μA DC
Emitter Cut off Current (V _{EB} = 5V dc I _C = 0)	I _{EBO}	1	100	
Second Breakdown				
Second Breakdown Collector Current with Base Forward Biased ($V_{CE} = 50V DC$, $t = 1s$ (non repetitive)) ($V_{CE} = 100V DC$, $t = 1s$ (non repetitive))	I _{S/b}	5 1	-	A DC
On Characteristic				
DC Current Gain (I _C = 5A DC, V _{CE} = 2V DC)	hfE	25	150	-
Collector-Emitter Saturation Voltage $(I_C = 5A DC, I_B = 0.5A DC)$	VCE (sat)	-	1	V DC
Base-Emitter On Voltage (I _C = 5A DC, V _{CE} = 2V DC)	VBE (on)	-	2	
Dynamic Characteristics				
Current-Gain - Bandwidth Product ($I_C = 0.5A$ DC, $V_{CE} = 10V$ DC, $f_{test} = 0.5MHz$)	f⊤	2	-	MHz
Output Capacitance $(V_{CB} = 10V DC, I_{E} = 0, f_{test} = 1MHz)$	Cob	-	1,000	pF

^{1.} Pulse Test : Pulse Width = 300µs, Duty Cycle ≤2%.

Active - Region Safe Operating Area



V_{CE}, Collector-Emitter Voltage (Volts)

There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate Ic - VCE limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than curves indicate. The data is based on TJ (PK) = 200°C; Tc is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values.

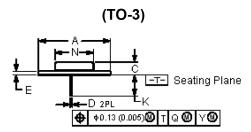
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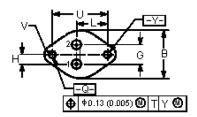


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Diagram





Style 1: Pin 1. Base 2. Emitter Collector (Case)

Dimensions	Minimum	Maximum	
А	1.55 (39.37) Reference		
В	-	1.05 (26.67)	
С	0.25 (6.35)	0.335 (8.51)	
D	0.038 (0.97)	0.043 (1.09)	
E	0.055 (1.4)	0.07 (1.77)	
G	0.43 (10.92) BSC		
Н	0.215 (5.46) BSC		
K	0.44 (11.18)	0.48 (12.19)	
L	0.665 (16.89) BSC		
N	-	0.83 (21.08)	
Q	0.151 (3.84)	0.165 (4.19)	
U	1.187 (30.15) BSC		
V	0.131 (3.33)	0.188 (4.77)	

Dimensions: Millimetres

Part Number Table

Description	Part Number
Transistor, NPN, TO-3	MJ15003

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